

TQP7M9104

2W High Linearity Amplifier



Applications

- Repeaters
- BTS Transceivers
- BTS High Power Amplifiers
- CDMA / WCDMA / LTE
- General Purpose Wireless

Product Features

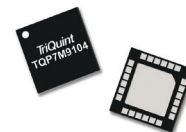
- 700-4000 MHz
- +32.8 dBm P1dB
- +49.5 dBm Output IP3
- 15.8 dB Gain @ 2140 MHz
- +5V Single Supply, 435 mA Collector Current
- Internal RF overdrive protection
- Internal DC overvoltage protection
- Internal Active Bias
- On chip ESD protection
- Shut-down Capability
- Capable of handling 10:1 VSWR @ 5Vcc, 2.14 GHz, 32.8 dBm CW Pout or 23.5 dBm WCDMA Pout

General Description

The TQP7M9104 is a high linearity driver amplifier in industry standard, RoHS compliant, QFN surface mount package. This InGaP/GaAs HBT delivers high performance across 700-4000 MHz range of frequencies with 15.8 dB Gain, +49.5 dBm OIP3 and +32.5 dBm P1dB at 2.14 GHz while only consuming 435 mA quiescent collector current. All devices are 100% RF and DC tested.

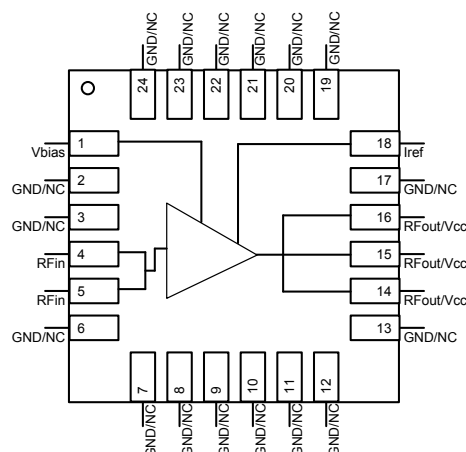
The TQP7M9104 incorporates on-chip features that differentiate it from other products in the market. The amplifier integrates an on-chip DC over-voltage and RF over-drive protection. This protects the amplifier from electrical DC voltage surges and high input RF input power levels that may occur in a system.

The TQP7M9104 is targeted for use as a driver amplifier in wireless infrastructure where high linearity, medium power, and high efficiency are required. The device is an excellent candidate for transceiver line cards and high power amplifiers in current and next generation multi-carrier 3G / 4G base stations.



24-pin QFN 4x4mm SMT Package

Functional Block Diagram



Pin Configuration

| Pin # | Symbol |
|--|-----------|
| 1 | Vbias |
| 2, 3, 6, 7, 8, 9, 10, 11, 12, 13, 17, 19, 20, 21, 22, 23, 24 | GND / NC |
| 4, 5 | RFIn |
| 14, 15, 16 | RFout/Vcc |
| 18 | Iref |

Ordering Information

| Part No. | Description |
|-------------------|------------------------------|
| TQP7M9104 | 2 W High Linearity Amplifier |
| TQP7M9104-PCB900 | TQP7M9104 920-960MHz EVB |
| TQP7M9104-PCB2140 | TQP7M9104 2.11-2.17GHz EVB |

Standard T/R size =2500 pieces on a 13" reel.

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Specifications

Absolute Maximum Ratings

| Parameter | Rating |
|--------------------------|----------------|
| Storage Temperature | -65 to +150 °C |
| Device Voltage, V_{cc} | 6.5 V |
| Maximum Input Power, CW | +30 dBm |

Operation of this device outside the parameter ranges given above may cause permanent damage.

Recommended Operating Conditions

| Parameter | Min | Typ | Max | Units |
|---|-----|-----|-------|-------|
| V_{cc} | | +5 | +5.25 | V |
| T_{case} | -40 | | +85 | °C |
| T_j (for >10 ⁶ hours MTTF) | | | 160 | °C |

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

Electrical Specifications

Test Conditions: $V_{CC} = +5V$, $I_{CQ} = 435$ mA, $T = 25^\circ C$ using a TQP7M9104-PCB2140 application circuit.

| Parameter | Conditions | Min | Typical | Max | Units |
|--|-------------|-------|---------|------|-------|
| Operational Bandwidth | | 700 | | 4000 | MHz |
| Test Frequency | | | 2140 | | MHz |
| Power Gain | | 14.3 | 15.8 | 17.3 | dB |
| Input Return Loss | | | 12 | | dB |
| Output Return Loss | | | 9.5 | | dB |
| Output IP3 (+17 dBm/tone, $\Delta f = 1$ MHz) | See Note 1. | +45.5 | +49.5 | | dBm |
| WCDMA Channel Power (at -50 dBc ACLR) | See Note 2. | | 23.8 | | dBm |
| Output P1dB | | +32 | +32.8 | | dBm |
| Noise Figure | | | 4.4 | | dB |
| Quiescent Collector Current, I_{CQ} | | 355 | 435 | 490 | mA |
| V_{cc} | | | +5 | | V |
| I_{ref} | | | 19 | | mA |
| Thermal Resistance (jnc to case) θ_{jc} | | | 15.7 | | °C/W |

Notes:

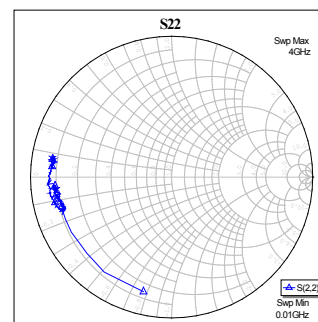
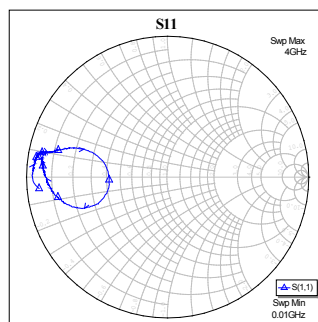
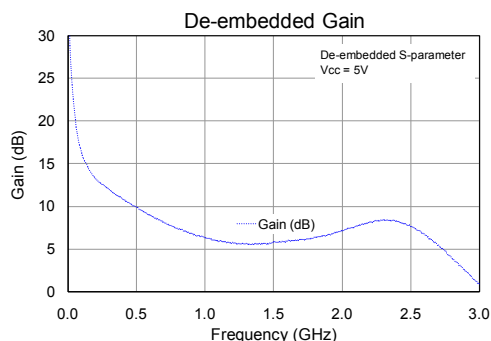
- OIP3 is measured with 1 MHz tone spacing.
- Using W-CDMA 3GPP Test Model 1+64 DPCH, PAR = 9.7 dB @ 0.01% Probability, 3.84 MHz BW

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Device Characterization Data



S-Parameter Data

$V_{dd} = +5\text{ V}$, $I_{cq} = 435\text{ mA}$, $I_{ref} = 19\text{ mA}$, $T = +25^\circ\text{C}$, unmatched 50 ohm system, calibrated to device leads

| Freq (MHz) | S11 (dB) | S11 (ang) | S21 (dB) | S21 (ang) | S12 (dB) | S12 (ang) | S22 (dB) | S22 (ang) |
|------------|----------|-----------|----------|-----------|----------|-----------|----------|-----------|
| 50 | -0.4553 | -179.26 | 20.126 | 118.98 | -43.273 | 4.1446 | -1.8524 | -155.37 |
| 100 | -0.4348 | 178.69 | 15.971 | 124.23 | -42.615 | -1.4433 | -1.8878 | -166.21 |
| 200 | -0.4583 | 176.36 | 13.24 | 126.46 | -40.235 | 2.3772 | -1.859 | -172.01 |
| 400 | -0.5124 | 173.38 | 10.778 | 118.38 | -40.956 | 0.7196 | -1.5792 | -174.84 |
| 600 | -0.5796 | 171.48 | 8.9263 | 108.51 | -41.682 | 10.901 | -1.6005 | -175.51 |
| 800 | -0.6594 | 170.04 | 7.3201 | 100.05 | -42.533 | -8.3414 | -1.6164 | -174.73 |
| 1000 | -0.7617 | 169.21 | 6.2878 | 93.94 | -42.841 | 6.4435 | -1.531 | -173.74 |
| 1200 | -0.8777 | 168.95 | 5.7693 | 89.116 | -40.461 | 3.1558 | -1.6296 | -171.43 |
| 1400 | -1.1121 | 168.56 | 5.5556 | 83.209 | -39.435 | -0.2787 | -1.7656 | -170.12 |
| 1600 | -1.4274 | 167.84 | 6.0222 | 74.67 | -41.097 | -1.3568 | -1.8812 | -167.74 |
| 1800 | -1.9525 | 165.88 | 6.3509 | 63.971 | -37.935 | -22.971 | -1.951 | -165.22 |
| 2000 | -3.0149 | 163.02 | 7.1412 | 51.862 | -36.666 | -37.917 | -1.9853 | -163.19 |
| 2200 | -5.3234 | 162.27 | 8.1891 | 30.583 | -35.423 | -57.21 | -1.7616 | -163.18 |
| 2400 | -7.8162 | -179.65 | 8.2216 | 2.8455 | -35.631 | -78.615 | -1.5099 | -167.05 |
| 2600 | -5.6951 | -159.12 | 6.6099 | -26.943 | -35.017 | -113.27 | -1.2811 | -172.58 |
| 2800 | -3.2673 | -161.75 | 3.8288 | -51.412 | -37.551 | -151.24 | -1.2268 | -179.96 |
| 3000 | -2.1416 | -169.16 | 0.9043 | -67.725 | -39.417 | -168.38 | -1.4503 | 175.32 |

TQP7M9104

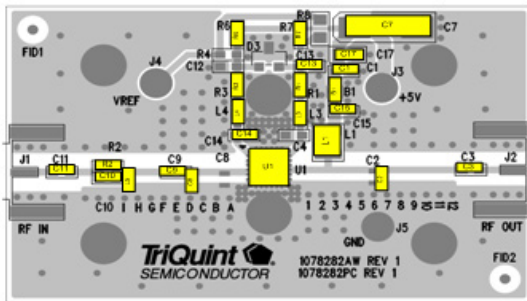
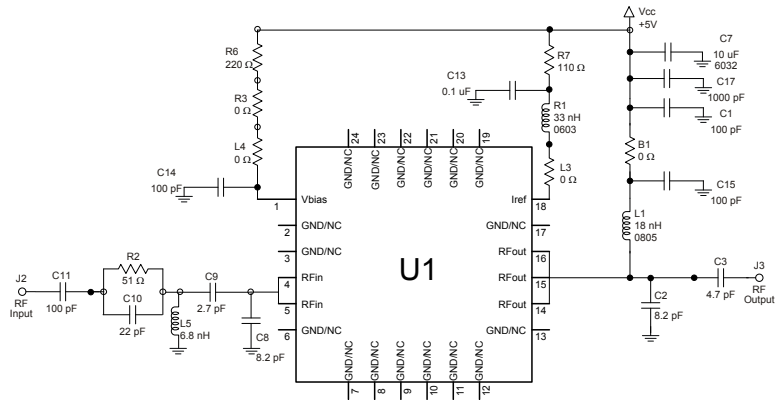
2W High Linearity Amplifier



Reference Design 869-894 MHz

Typical Performance at 25 °C

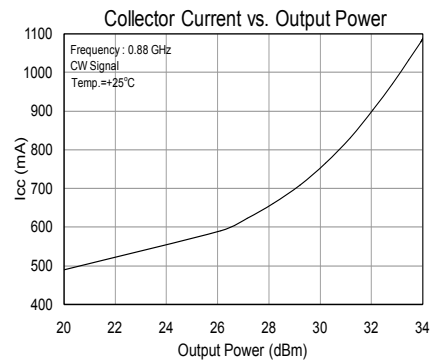
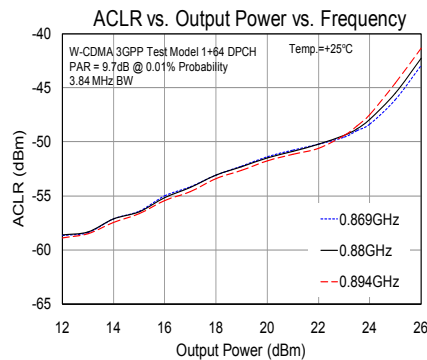
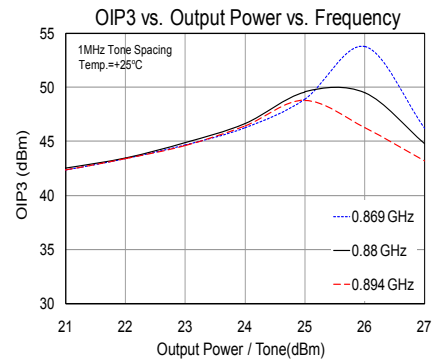
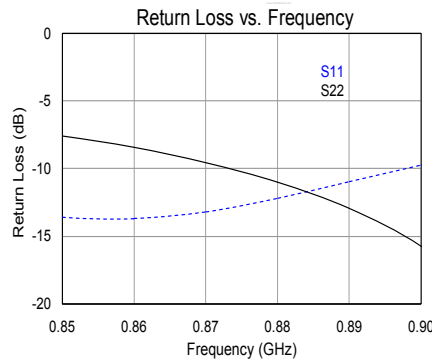
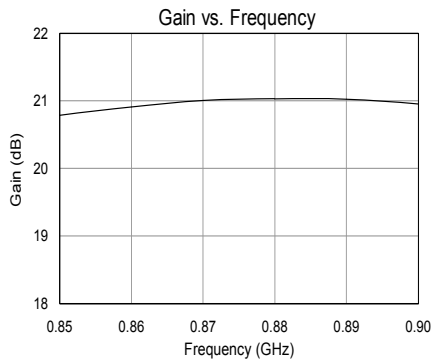
| Frequency (MHz) | Units | 869 | 880 | 894 |
|--|-------|-------|-------|-------|
| Gain | dB | 20.8 | 20.8 | 20.8 |
| Input Return Loss | dB | -13.3 | -13 | -11.5 |
| Output Return Loss | dB | -7.7 | -8.6 | -9.8 |
| Output P1dB | dBm | +34.3 | +34.1 | +33.8 |
| Output IP3 (+23 dBm/100 Hz, Δf = 1 MHz) | dBm | +44.9 | +44.9 | +44.7 |
| WCDMA Channel Power (at -50 dBc ACLR) | dB | 22 | 22.5 | 23 |
| Supply Voltage, Vcc | V | +5 | | |
| Quiescent Current, Icq | mA | 435 | | |
| Reference Current, Iref | mA | 19 | | |



Notes:

- Components shown on the silkscreen but not on the schematic are not used.
- 0 Ω resistor may be replaced with copper trace in the target application layout.
- Iref can be used as device power down current by placing R7 at location R8.
- The recommended component values are dependent upon the frequency of operation.
- All components are of 0603 size unless stated on the schematic.
- R1 is critical for device linearity performance.
- Critical component placement locations:
Distance between center of C8 and TQP7M9104 (U1) device package is 243 mil.
Distance between center of L5 and TQP7M9104 (U1) device package is 452 mil.
Distance between center of C2 and TQP7M9104 (U1) device package is 355 mil.
Distance between center of C9 and TQP7M9104 (U1) device package is 275 mil.

RF Performance Plots 869-894 MHz

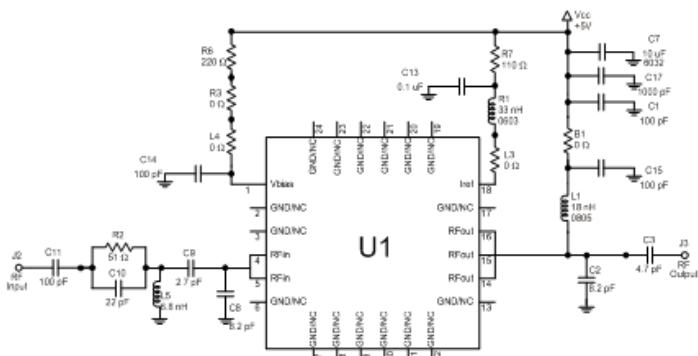
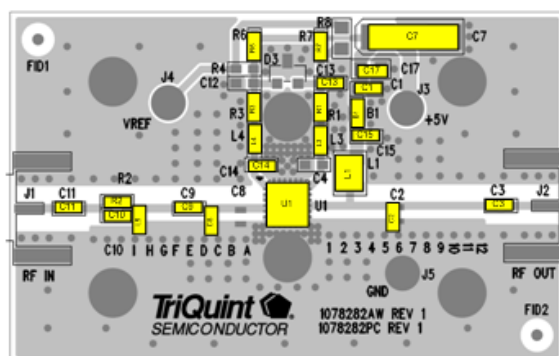


TQP7M9104

2W High Linearity Amplifier



Application Circuit 920-960 MHz (TQP7M9104-PCB900)



Notes:

1. See PC Board Layout under Application Information section for more information.
2. Components shown on the silkscreen but not on the schematic are not used.
3. 0 Ω resistor may be replaced with copper trace in the target application layout.
4. Iref can be used as device power down current by placing R7 at location R8.
5. The recommended component values are dependent upon the frequency of operation.
6. All components are of 0603 size unless stated on the schematic.
7. R1 is critical for device linearity performance.
8. Critical component placement locations:
 Distance between center of C8 and TQP7M9104 (U1) device package is 190 mil.
 Distance between center of L5 and TQP7M9104 (U1) device package is 452 mil.
 Distance between center of C2 and TQP7M9104 (U1) device package is 305 mil.
 Distance between center of C9 and TQP7M9104 (U1) device package is 275 mil.

Bill of Material

| RefDes | Value | Description | Manuf. | Part Number |
|---------------------|--------------|--|-----------|----------------|
| U1 | n/a | 2W High Linearity Amplifier | TriQuint | TQP7M9104 |
| n/a | n/a | Printed Circuit Board | TriQuint | 1078282 |
| C9 | 2.7 pF | Capacitor, Chip, 0603, ± 0.05 pF, 50 V, Accu-P | AVX | 06035J2R7ABSTR |
| B1, L3, L4, R3 | 0 Ω | Resistor, Chip, 0603, 5%, 1/16W | various | |
| L5 | 6.8 nH | Inductor, 0603, 5% | Toko | LL1608-FSL6N8 |
| C3 | 4.7 pF | Capacitor, Chip, 0603, ± 0.05 pF, 50 V, Accu-P | AVX | 06035J4R7ABSTR |
| C2, C8 | 8.2 pF | Capacitor, Chip, 0603, ± 0.05 pF, 50 V, Accu-P | AVX | 06035J8R2ABSTR |
| C10 | 22 pF | Capacitor, Chip, 0603, 5%, 50 V, NPO/COG | various | |
| C1, C14, C15, C11 | 100 pF | Capacitor, Chip, 0603, 5%, 50V, NPO/COG | various | |
| L1 | 18 nH | Inductor, 0805, 5%, Coilcraft CS Series | Coilcraft | 0805CS-330XJLB |
| C17 | 1000 pF | Capacitor, Chip, 0603, 10%, 50V, NPO/COG | various | |
| C13 | 0.1 μ F | Capacitor, Chip, 0603, 50V, X5R, 10% | various | |
| C7 | 10 μ F | Capacitor, Tantalum, 6032, 35V, 10% | various | |
| R2 | 51 Ω | Resistor, Chip, 0603, 5%, 1/16W | various | |
| R6 | 220 Ω | Resistor, Chip, 0603, 1%, 1/16W | various | |
| R7 | 110 Ω | Resistor, Chip, 0603, 1%, 1/16W | various | |
| R1 | 33 nH | Inductor, 0603, 5% | Toko | LL1608-FSL33N |
| R8, R4, C12, C4, D3 | n/a | Do Not Place | | |

TQP7M9104

2W High Linearity Amplifier



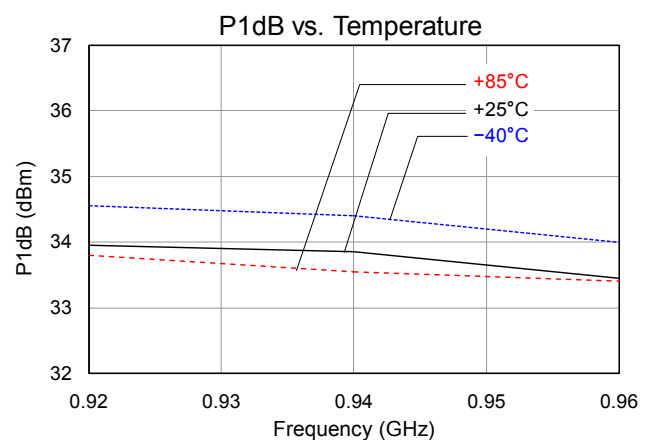
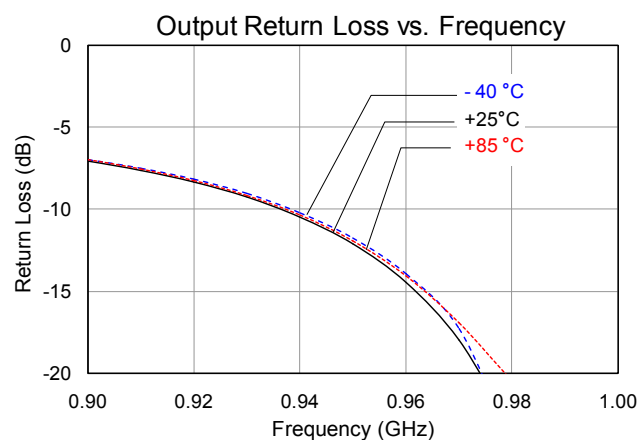
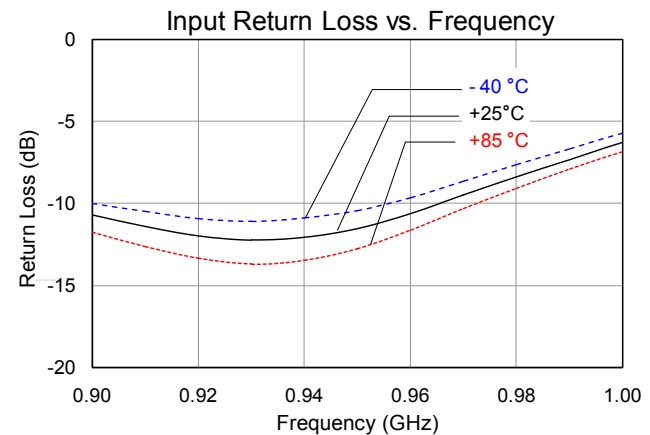
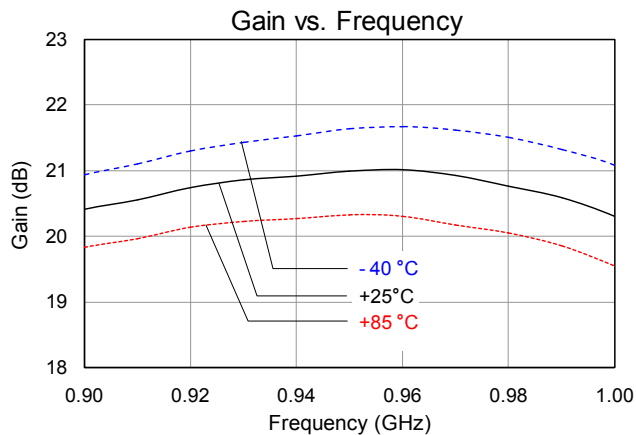
Typical Performance 920-960 MHz

| Frequency | MHz | 920 | 940 | 960 |
|---|-----|-------|-------|-------|
| Gain | dB | 20.8 | 21 | 21 |
| Input Return Loss | dB | -13 | -12 | -11 |
| Output Return Loss | dB | -9 | -11.8 | -15 |
| Output P1dB | dBm | +33.9 | +33.8 | +33.4 |
| Output IP3 (+23 dBm/tone, $\Delta f = 1$ MHz) | dBm | +45 | +45 | +45 |
| WCDMA Channel power (at -50 dBc ACLR) [1] | dBm | +24 | +23.5 | +23 |
| Supply Voltage, Vcc | V | +5 | | |
| Quiescent Collector Current, Icq | mA | 435 | | |
| Reference Current, Iref | mA | 19 | | |

Notes:

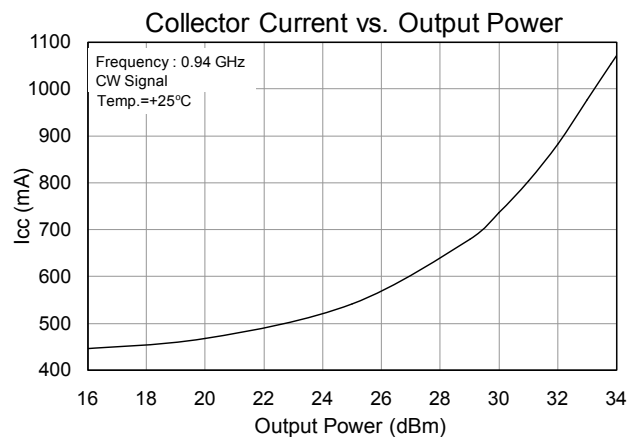
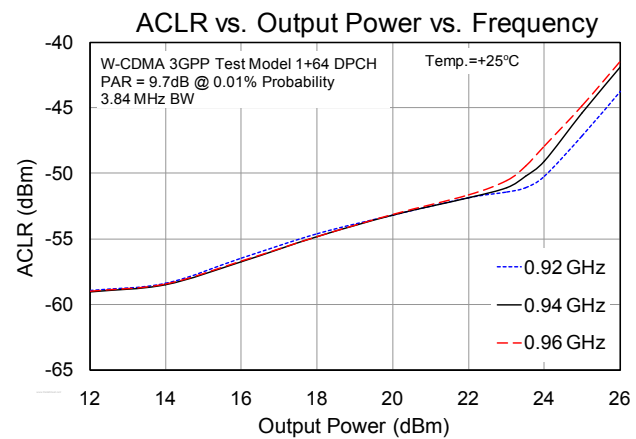
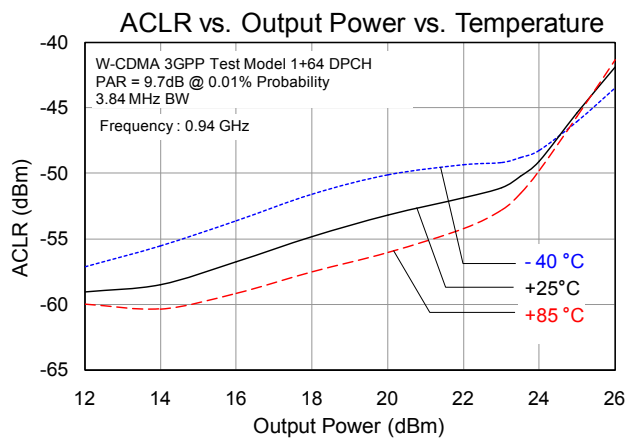
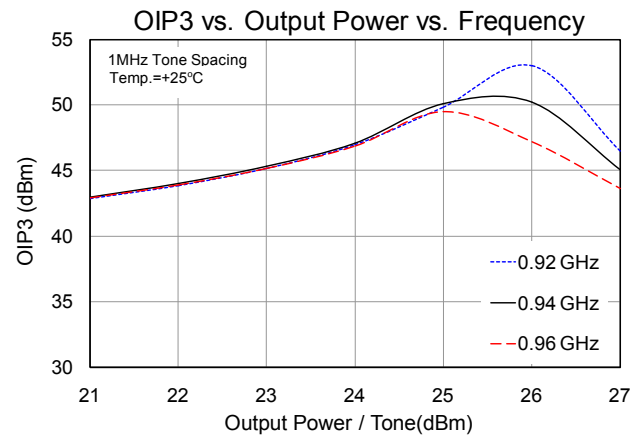
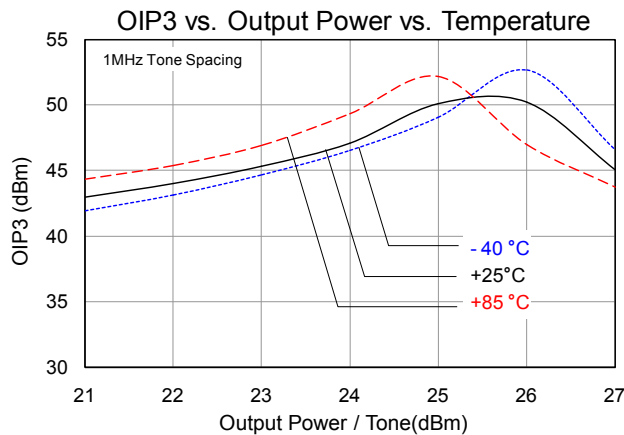
1. ACLR Test set-up: 3GPP WCDMA, TM1+64 DPCH, +5 MHz offset, PAR = 9.7 dB at 0.01% Prob.

RF Performance Plots 920-960 MHz



TQP7M9104

2W High Linearity Amplifier

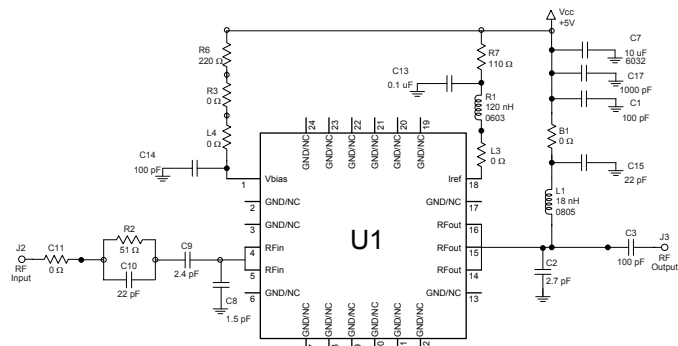
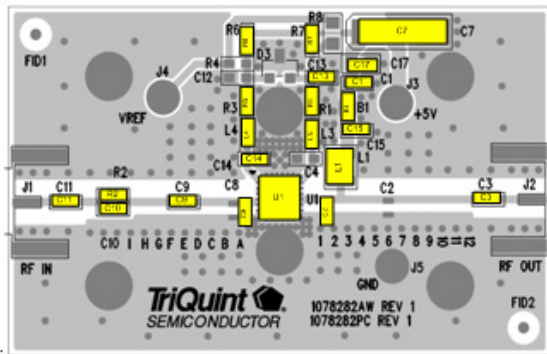


TQP7M9104

2W High Linearity Amplifier



Application Circuit 2110-2170 MHz (TQP7M9104-PCB2140)



Notes:

1. See PC Board Layout under Application Information section for more information.
2. Components shown on the silkscreen but not on the schematic are not used.
3. 0 Ω resistor may be replaced with copper trace in the target application layout.
4. Iref can be used as device power down current by placing R7 at location R8.
5. The recommended component values are dependent upon the frequency of operation.
6. All components are of 0603 size unless stated on the schematic.
7. R1 is critical for device linearity performance.
8. Critical component placement locations:
 - Distance between center of C8 and TQP7M9104 (U1) device package is 50 mil.
 - Distance between center of C2 and TQP7M9104 (U1) device package is 113 mil.
 - Distance between center of C9 and TQP7M9104 (U1) device package is 275 mil.

Bill of Material

| Ref Des | Value | Description | Manuf. | Part Number |
|---------------------|--------------|---|-----------|----------------|
| U1 | n/a | 2W High Linearity Amplifier | TriQuint | TQP7M9104 |
| n/a | n/a | Printed Circuit Board | TriQuint | 1078282 |
| C8 | 1.5 pF | Capacitor, Chip, 0603, ± 0.05 pF, 50V, Accu-P | AVX | 06035J1R5ABSTR |
| C9 | 2.4 pF | Capacitor, Chip, 0603, ± 0.05 pF, 50V, Accu-P | AVX | 06035J2R4ABSTR |
| C2 | 2.7 pF | Capacitor, Chip, 0603, ± 0.05 pF, 50V, Accu-P | AVX | 06035J2R7ABSTR |
| B1, L3, L4, R3, C11 | 0 Ω | Resistor, Chip, 0603, 5%, 1/16W | various | |
| C10, C15 | 22 pF | Capacitor, Chip, 0603, 5%, 50V, NPO/COG | various | |
| C1, C14, C3 | 100 pF | Capacitor, Chip, 0603, 5%, 50V, NPO/COG | various | |
| L1 | 18 nH | Inductor, 1008, 5%, Ceramic | Coilcraft | 1008HQ-18NXJL |
| C17 | 1000 pF | Capacitor, Chip, 0603, 10%, 50V, NPO/COG | various | |
| C13 | 0.1 uF | Capacitor, Chip, 0603, 10%, 50V, X5R | various | |
| C7 | 10 uF | Capacitor, Tantalum, 6032, 20 %, 50V | various | |
| R2 | 51 Ω | Resistor, Chip, 0603, 5%, 1/16W | various | |
| R6 | 220 Ω | Resistor, Chip, 0603, 1%, 1/16W | various | |
| R7 | 110 Ω | Resistor, Chip, 0603, 1%, 1/16W | various | |
| R1 | 120 nH | Inductor, 0603, 5% | Toko | LL1608-FSR12J |
| R8, R4, C12, C4, D3 | n/a | Do Not Place | | |

| Frequency | MHz | 2110 | 2140 | 2170 |
|-----------|-----|------|------|------|
|-----------|-----|------|------|------|

TQP7M9104

2W High Linearity Amplifier

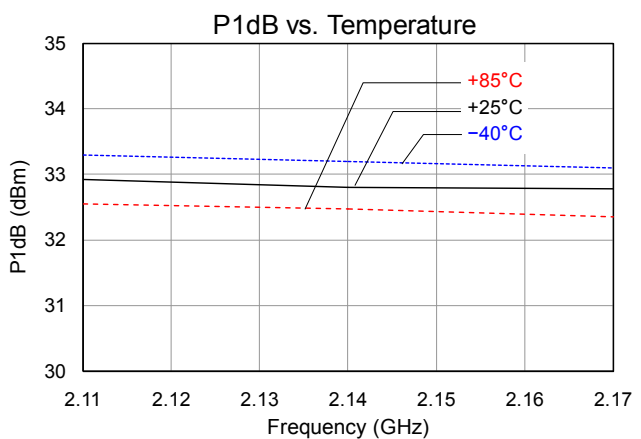
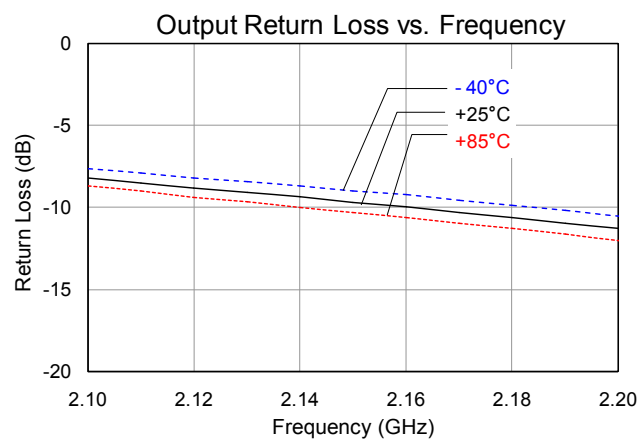
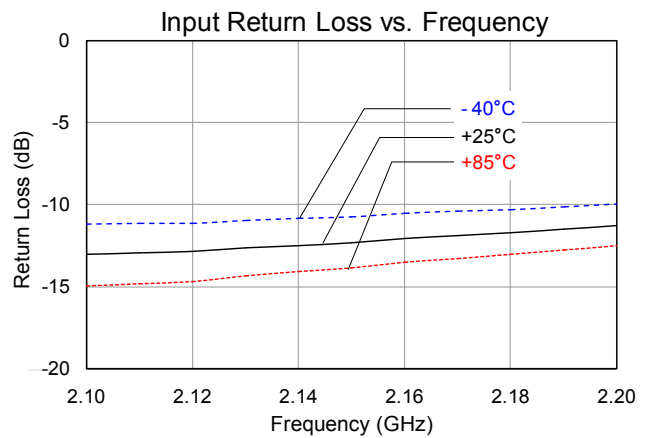
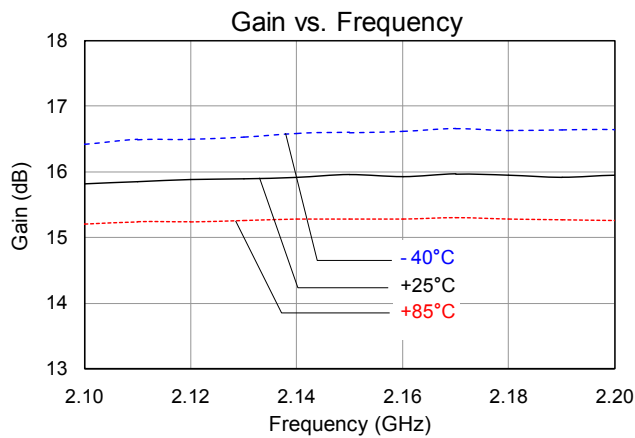


| | | | | |
|---|-----|-------|-------|-------|
| Gain | dB | 15.8 | 15.8 | 15.8 |
| Input Return Loss | dB | -12.4 | -12.0 | -11.8 |
| Output Return Loss | dB | -8.7 | -9.5 | -10.5 |
| Output P1dB | dBm | +32.9 | +32.8 | +32.8 |
| Output IP3 (+17 dBm/tone, $\Delta f = 1$ MHz) | dBm | +49 | +49.5 | +50 |
| WCDMA Channel power (at -50 dBc ACLR) [1] | dBm | +23.5 | +23.8 | +24.0 |
| Noise Figure | dB | 4.4 | 4.4 | 4.6 |
| Supply Voltage, Vcc | V | +5 | | |
| Quiescent Collector Current, Icq | mA | 435 | | |
| Reference Current, Iref | mA | 19 | | |

Notes:

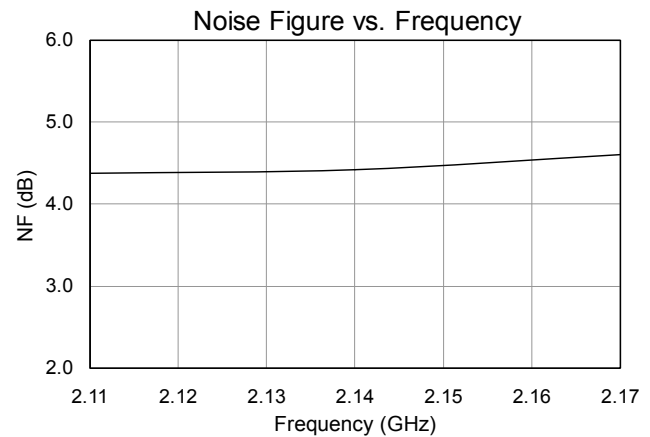
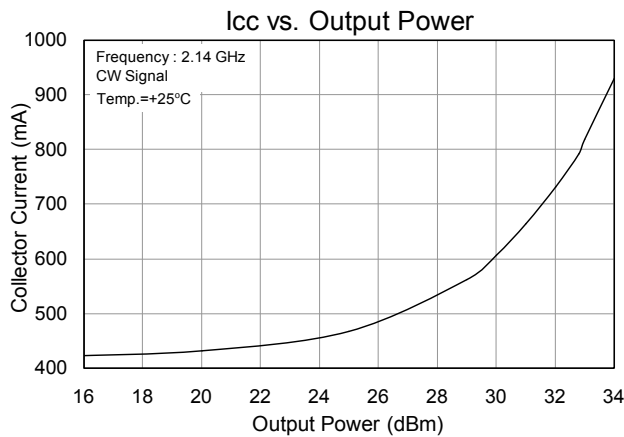
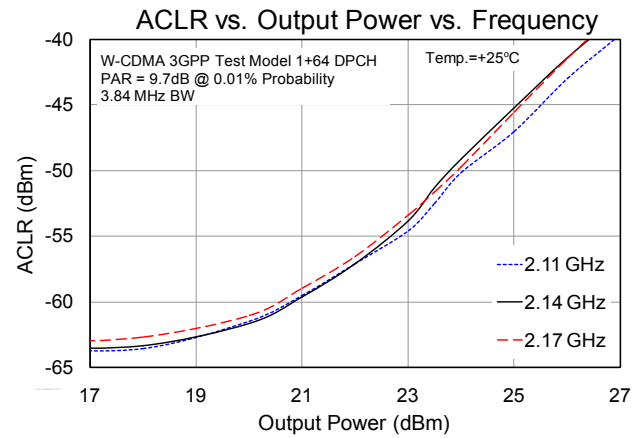
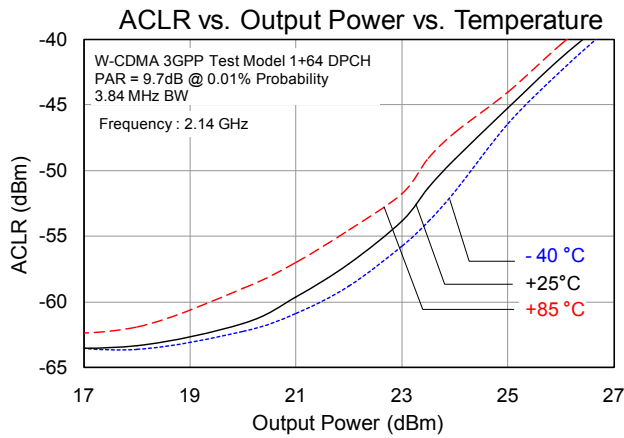
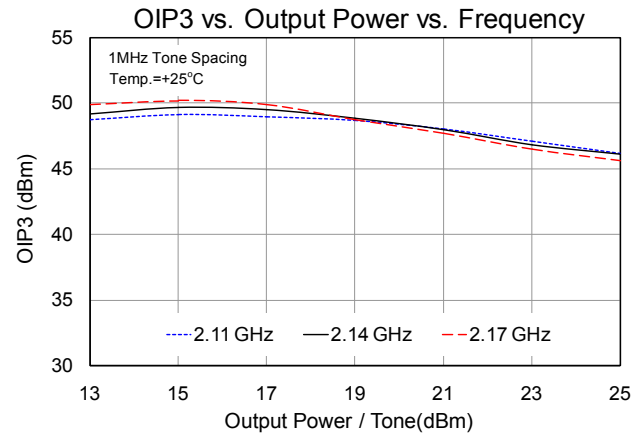
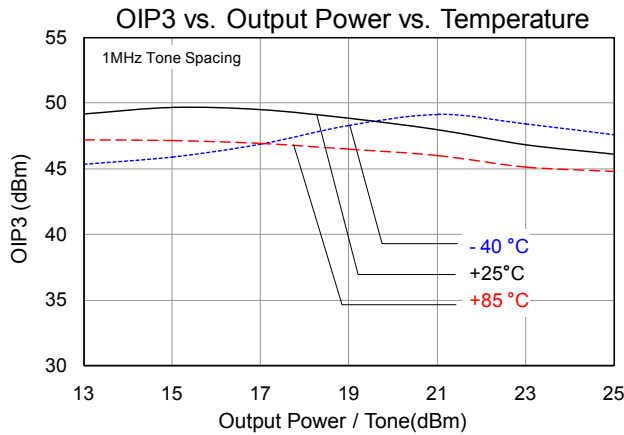
1. ACLR Test set-up: 3GPP WCDMA, TM1+64 DPCH, +5 MHz offset, PAR = 9.7 dB at 0.01% Prob.

RF Performance Plots 2110-2170 MHz



TQP7M9104

2W High Linearity Amplifier

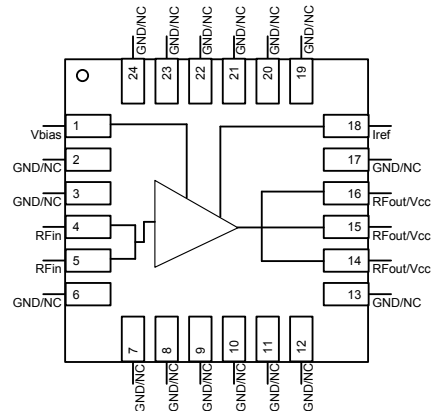


TQP7M9104

2W High Linearity Amplifier



Pin Configuration and Description



| Pin | Symbol | Description |
|--|-------------|---|
| 1 | Vbias | Voltage supply for active bias for the amp. Connect to same supply voltage as Vcc. |
| 2, 3, 6, 7, 8, 9, 10, 11, 12, 13, 17, 19, 20, 21, 22, 23, 24 | GND/NC | No internal connection. This pin can be grounded or N/C on PCB. Land pads should be provided for PCB mounting integrity. |
| 4, 5 | RFin | RF Input. DC voltage present, blocking capacitor required. Requires external match for optimal performance. |
| 14, 15, 16 | RFout / Vcc | RF Output. DC Voltage present, blocking cap required. Requires external match for optimal performance. |
| 18 | Iref | Reference current into internal active bias current mirror. Current into Iref sets device quiescent current. Also, can be used as on/off control. |
| Backside paddle | RF/DC GND | Multiple Vias should be employed to minimize inductance and thermal resistance. Use recommended via pattern shown under mounting configuration and ensure good solder attach for optimum thermal and electrical performance |

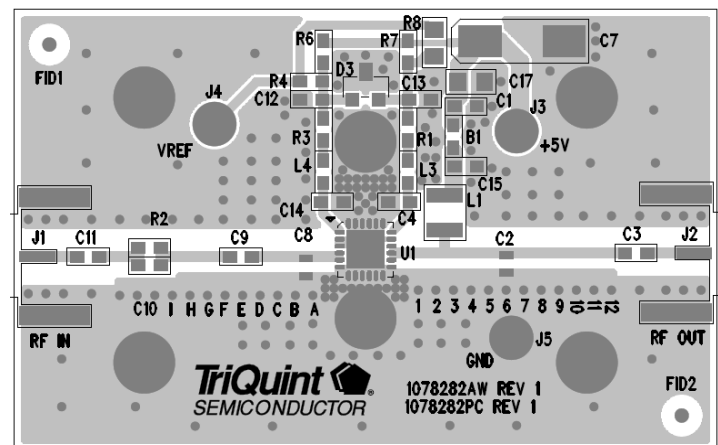
Applications Information

PC Board Layout

PCB Material (stackup):

- 1 oz. Cu top layer
- 0.014 inch Nelco N4000-13, $\epsilon_r=3.7$
- 1 oz. Cu middle layer 1
- Core Nelco N4000-13
- 1 oz. Cu middle layer 2
- 0.014 inch Nelco N-4000-13
- 1 oz. Cu bottom layer
- Finished board thickness is 0.062±.006
- 50 ohm line dimensions: width = .028"

The pad pattern shown has been developed and tested for optimized assembly at TriQuint Semiconductor. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from supplier to supplier, careful process development is recommended.



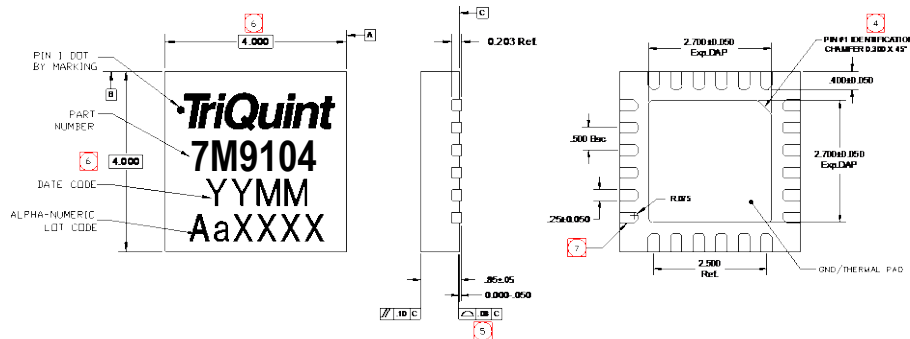
Package Information and Dimensions

This package is lead-free, RoHS-compliant, and green. The plating material on the pins is annealed matte tin over copper. It is compatible with both lead-free (maximum 260 °C reflow temperature) and leaded (maximum 245 °C reflow temperature) soldering processes.

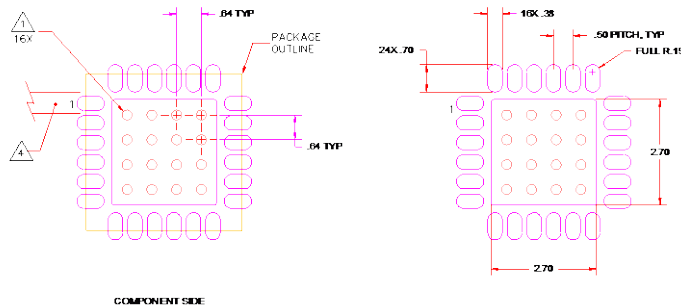
The component will be laser marked with “7M9104” product label with an alphanumeric lot code on the top surface of the package.

NOTES:

- | | | | |
|----|--|----|--|
| 1. | EXCEPT WHERE NOTED, THIS PART OUTLINE CONFORMS TO JEDEC STANDARD MO-220, ISSUE C (VARIATION VGGC) FOR THERMALLY ENHANCED PLASTIC VERY THIN FINE PITCH QUAD FLAT NO LEAD PACKAGE (DFN). | 4. | THE TERMINAL #1 IDENTIFIER AND TERMINAL NUMBERING CONVENTION CONFORM TO JEDEC 95-1 SPP-012 |
| 2. | DIMENSIONING & TOLERANCING CONFORM TO ASME Y14.4M-1994 | 5. | COPLANARITY APPLIES TO THE EXPOSED GROUND/THERMAL PAD AS WELL AS THE TERMINALS |
| 3. | ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES. | 6. | PACKAGE BODY LENGTH/WIDTH DOES NOT INCLUDE PLASTIC FLASH PROTRUSION ACROSS MOLD PARTING LINE |
| | | 7. | DEVIATION FROM JEDEC STANDARD MO-229, ISSUE C, 12 LEAD COUNT NOT |



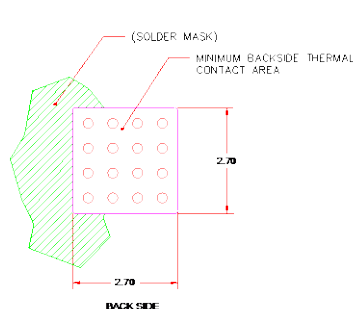
Mounting Configuration



All dimensions are in millimeters (inches).
Angles are in degrees.

Notes:

1. Ground vias are critical for the proper RF performance of this device. Vias should use a .35mm (#80 / .0135") diameter drill and have a final plated thru diameter of .25 mm (.010").
2. Add as much copper as possible to inner and outer layers near the part to ensure optimal thermal performance.



NOTES:

1. GROUND/THERMAL VIAS ARE CRITICAL FOR THE PROPER PERFORMANCE OF THIS DEVICE. VIAS SHOULD USE A 35mm (#80/0135") DIAMETER DRILL AND HAVE A FINAL PLATED THRU DIAMETER OF 25mm (.010").
2. ADD AS MUCH COPPER AS POSSIBLE TO INNER AND OUTER LAYERS NEAR THE PART TO ENSURE OPTIMAL THERMAL PERFORMANCE.
3. TO ENSURE RELIABLE OPERATION, DEVICE GROUND PAD/TO-GROUND PAD SOLDER JOINT IS CRITICAL
4. IF TRACE WIDTH DEPENDS UPON THE PC BOARD MATERIAL AND CONSTRUCTION
5. USE 1 OZ. COPPER MINIMUM.
6. ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES.

Product Compliance Information

ESD Information



Caution! ESD-Sensitive Device

ESD Rating: Class 1C
Value: ≥ 1000 V and < 2000 V
Test: Human Body Model (HBM)
Standard: JEDEC Standard JESD22-A114

ESD Rating: Class IV
Value: ≥ 1000 V min
Test: Charged Device Model (CDM)
Standard: JEDEC Standard JESD22-C101

MSL Rating

The part is rated Moisture Sensitivity Level 1 at 260°C per JEDEC standard IPC/JEDEC J-STD-020.

Solderability

The plating material on the pins is annealed matte tin over copper.

Compatible with both lead-free (maximum 260 °C reflow temperature) and tin/lead (maximum 245 °C reflow temperature) soldering processes.

This part is compliant with EU 2002/95/EC RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment).

This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C₁₅H₁₂Br₄O₂) Free
- PFOS Free
- SVHC Free

Contact Information

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